12. (Amended) An electrostatic discharge device formed in a first semiconductor material, the device comprising:

a collector region of a first conductivity type formed in the first semiconductor material;

a base region of a second conductivity type formed in the collector region;

an emitter formed on the first semiconductor material on the base region, the emitter having a top surface and a width;

a base extender formed on the first semiconductor material on the base region, the base extender being formed from a second semiconductor material that is different from the first semiconductor material;

B1 cont.

a layer of dielectric material formed on the first semiconductor material on the base region;

an ohmic emitter contact formed through the dielectric layer, the emitter contact having a top surface, contacting the top surface of the emitter, and having a width that is greater than the width of the emitter; and

an ohmic base contact formed through the layer of dielectric material, the base contact having a top surface, contacting the top surface of the base extender, being electrically connected to the base region, and having a width that is less than the width of the emitter contact, the ohmic base contact being formed from a third semiconductor material different from the second semiconductor material.

13. (Amended) The device of claim 12 wherein the emitter and the base extender are polysilicon.

Please add the following new claims:

B2

--23. The device of claim 12 and further comprising a first trace formed on the layer of dielectric material and the emitter contact.

24. The device of claim 23 and further comprising:

a second layer of dielectric material formed on the first layer of dielectric material and the first trace;

B2 cont.

a via formed through the second layer of dielectric material to make an electrical contact with the first trace; and

a second trace formed on the second layer of dielectric material to make an electrical contact with the via.--